

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

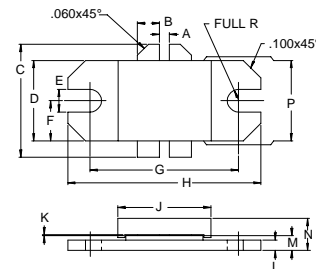
The **ASI TVU025** is Designed for Television Band IV & V Applications up to 860 MHz.

**FEATURES:**

- Common Emitter
- $P_G = 8.0$  dB at 25 W/860 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	8.0 A
$V_{CBO}$	45 V
$V_{CEO}$	30 V
$V_{EBO}$	3.0 V
$P_{DISS}$	135 W @ $T_C = 25$ °C
$T_J$	-50 °C to +200 °C
$T_{STG}$	-50 °C to +150 °C
$\theta_{JC}$	1.3 °C/W

**PACKAGE STYLE .450 BAL FLG(A)**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.055 / 1.40	
B	.120 / 3.05	.130 / 3.30
C	.785 / 19.94	
D	.455 / 11.56	.465 / 11.81
E	.120 / 3.05	.130 / 3.30
F	.230 / 5.84	
G	.838 / 21.28	.850 / 21.59
H	1.095 / 27.81	1.105 / 28.07
J	.525 / 13.34	.535 / 13.59
K	.002 / 0.05	.005 / 0.15
L	.055 / 1.40	.065 / 1.65
M	.080 / 2.03	.095 / 2.41
N	.195 / 4.95	
P	.445 / 11.30	.455 / 11.56

**ORDER CODE: ASI10650**
**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 50$ mA	45			V
$BV_{CEO}$	$I_C = 200$ mA	30			V
$BV_{EBO}$	$I_E = 10$ mA	3.0			V
$I_{CEO}$	$V_{CE} = 25$ V			5.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 3.0$ A	10		80	---
$C_{OB}$	$V_{CB} = 28$ V $f = 1.0$ MHz		70		pF
$P_G$	$V_{CE} = 25$ V $I_C = 3.2$ A $f = 860$ MHz	8.0			dB
$IMD_1$	$P_{OUT} = 25$ W	-45			dBc

This datasheet has been download from:

[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.